

N-channel TrenchMOS logic level FET 28 July 2016

**Product data sheet** 

### 1. General description

Logic level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with Vgst(th) rating of greater than 0.5V at 175 °C

### 3. Applications

- 12V, 24V and 48V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	120	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	349	W
Static charact	eristics			1			
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>		-	4.62	5.8	mΩ
Dynamic char	acteristics	·					
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 80 V; Fig. 13; Fig. 14		-	51	-	nC

[1] Continuous current is limited by package.

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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UF4
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

# 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK965R8-100E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK965R8-100E	BUK965R8-100E

### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	100	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	100	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-10	10	V
		$T_j \le 175 \ ^{\circ}C; Pulsed$	[1][2]	-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	349	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>	[3]	-	120	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>		-	105	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3		-	591	А
T <sub>stg</sub>	storage temperature			-55	175	°C
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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	175	°C
Source-drain	n diode					
l <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[3]	-	120	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	591	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{split} I_D &= 120 \text{ A};  \text{V}_{\text{sup}} \leq 100  \text{V};  \text{R}_{\text{GS}} = 50  \Omega; \\  \text{V}_{\text{GS}} &= 5  \text{V};  \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 4} \end{split}$	[4][5]	-	385	mJ

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering Tj and or VGS
- [3] Continuous current is limited by package.
- [4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [5] Refer to application note AN10273 for further information.

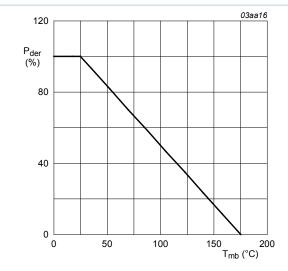


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

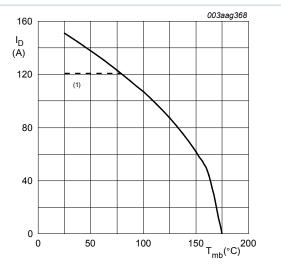
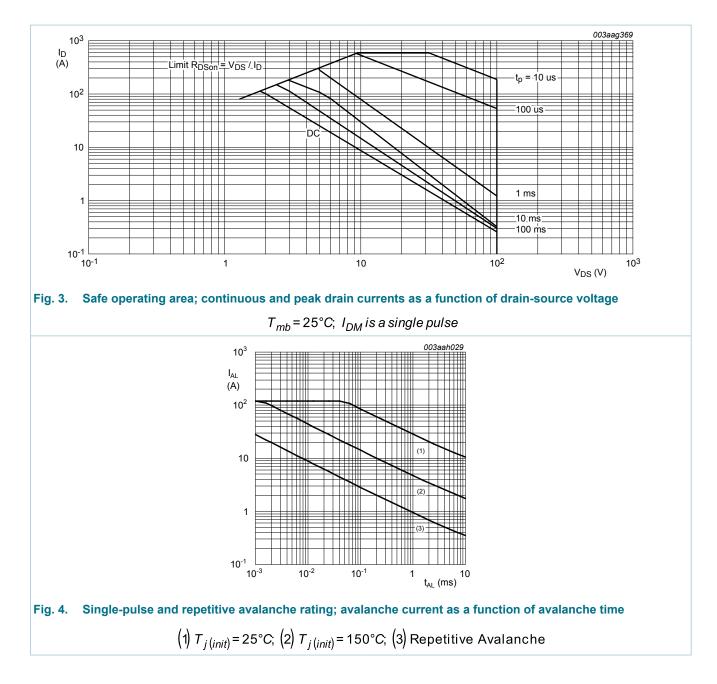


Fig. 2. Continuous drain current as a function of mounting base temperature

#### $V_{GS} \ge 5V$ (1) Capped at 120 A due to package.

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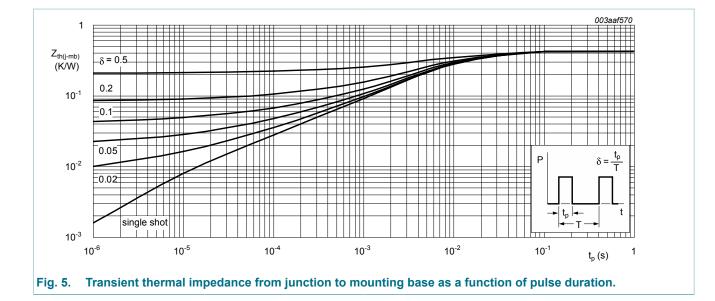
### 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.43	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

#### Table 6. Thermal characteristics

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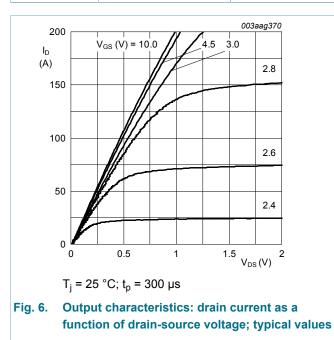


### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·				
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	90	-	-	V
V <sub>GS(th)</sub> gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	1.4	1.7	2.1	V	
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V	
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.5	-	-	V	
I <sub>DSS</sub> drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.05	1	μA	
	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA	
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub> drain-source on-state		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	4.62	5.8	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	4.45	5.6	mΩ
	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	-	16	mΩ	
Dynamic cł	naracteristics			1		
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 80 V; $V_{GS}$ = 5 V;	-	133	-	nC
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	23	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Q <sub>GD</sub>	gate-drain charge		-	51	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS}$ = 0 V; $V_{DS}$ = 25 V; f = 1 MHz;	-	13100	17460	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	 -	725	870	pF
C <sub>rss</sub>	reverse transfer capacitance		-	450	620	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 80 V; R <sub>L</sub> = 3.2 Ω; V <sub>GS</sub> = 5 V;	-	81	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	168	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	237	-	ns
t <sub>f</sub>	fall time		-	148	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-dra	in diode	· · · · · ·				
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>	-	0.77	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	70	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V	-	202	-	nC



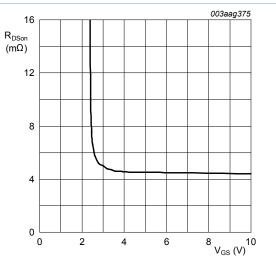
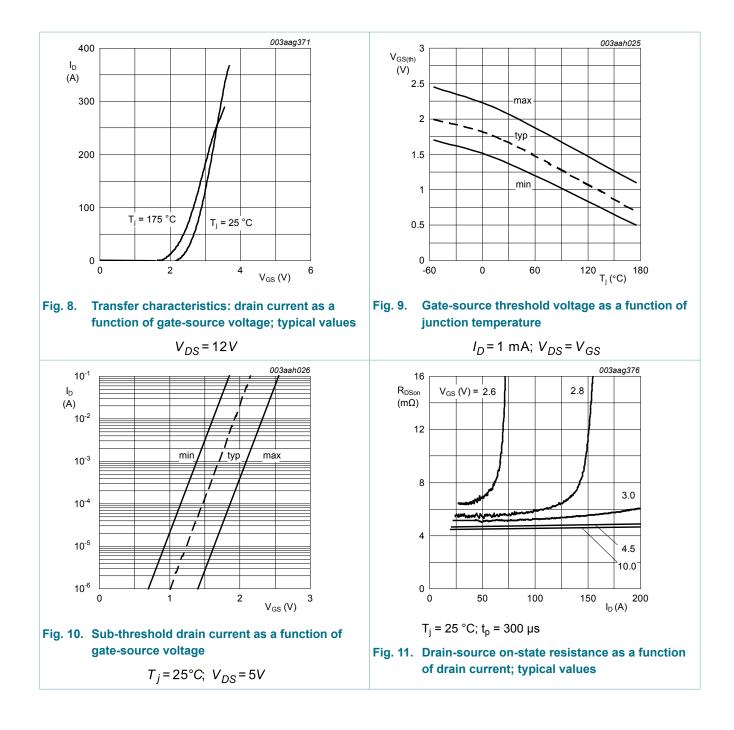


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25 \,^{\circ}C; I_D = 25A$ 

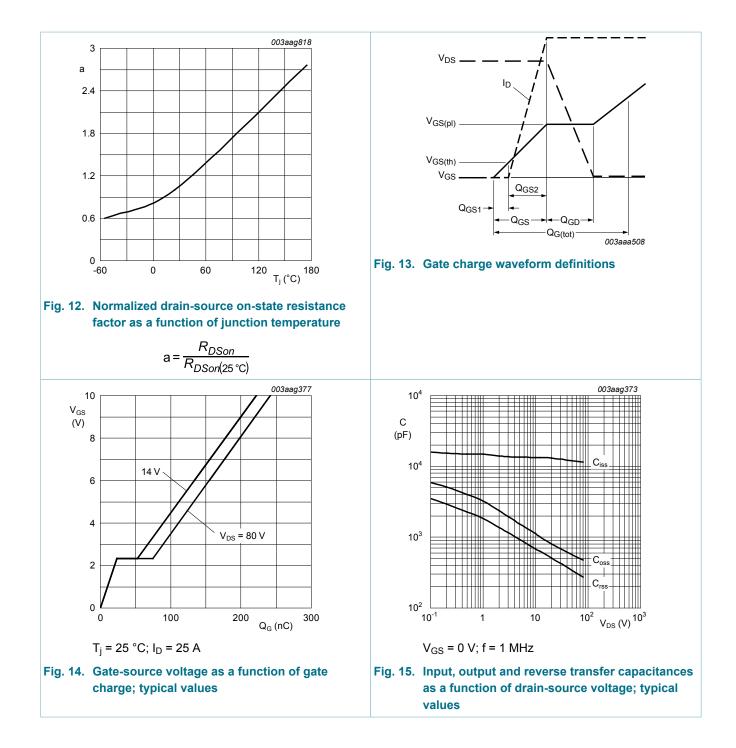
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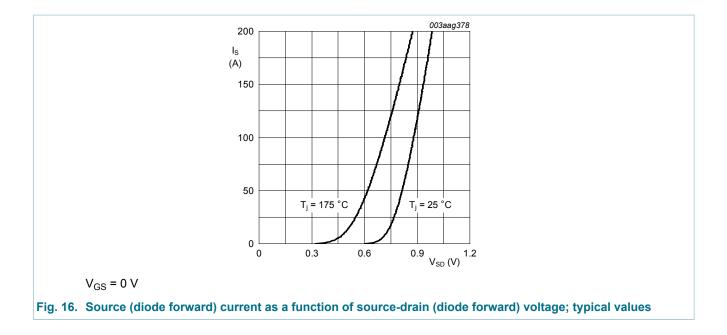
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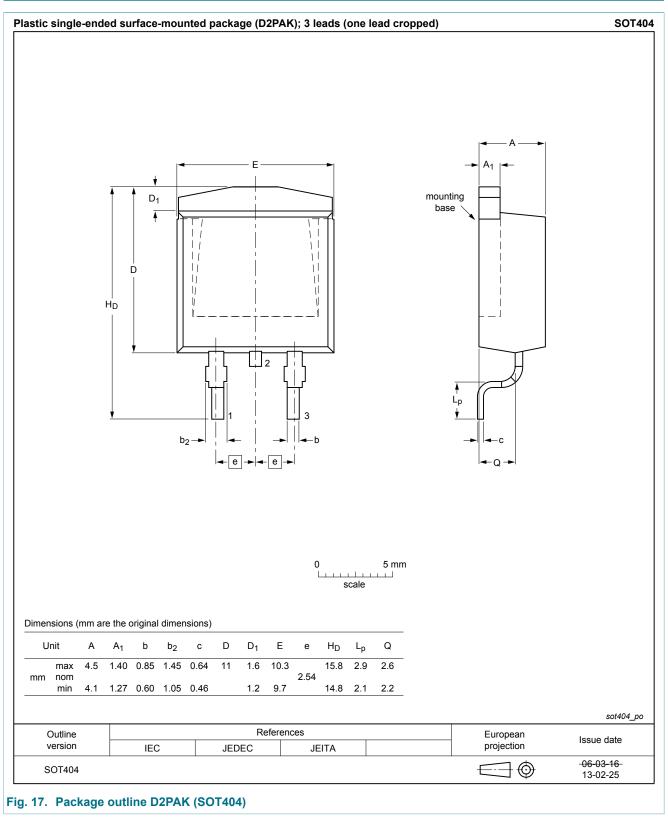
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### 11. Package outline



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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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